

UTC UNISONIC TECHNOLOGIES CO., LTD

8050S

NPN SILICON TRANSISTOR

LOW VOLTAGE HIGH **CURRENT SMALL SIGNAL** NPN TRANSISTOR

DESCRIPTION

The UTC 8050S is a low voltage high current small signal NPN transistor, designed for Class B push-pull audio amplifier and general purpose applications.

FEATURES

- * Collector current up to 700mA
- * Collector-Emitter voltage up to 20V
- * Complementary to UTC 8550S

ORDERING INFORMATION

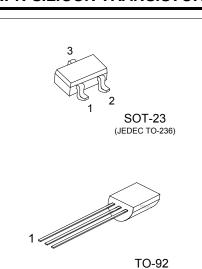
Ordering Number		Deelvere	Pin	Assignn	Deeking		
Lead Free	Halogen-Free	Package	1	2	3	Packing	
8050SL-x-AE3-R	8050SG-x-AE3-R	SOT-23	В	Е	С	Tape Reel	
8050SL-x-T92-B	8050SG-x-T92-B	TO-92	Е	С	В	Таре Вох	
8050SL-x-T92-K	8050SG-x-T92-K	TO-92	Е	С	В	Bulk	
Noto: Din Assignment: D: Dess	E: Emitter C: Cellecter						

Note: Pin Assignment: B: Base E: Emitter C: Collector

8050SG-x-AE3-R (1)Packing Type (2)Package Type (3)Rank (4)Green Package	 (1) R: Tape Reel, B: Tape Box, K: Bulk (2) AE3: SOT-23, T92: TO-92 (3) x: refer to Classification of h_{FE2} (4) G: Halogen Free and Lead Free L: Lead Free
(4)Green Package	(4) G: Halogen Free and Lead Free, L: Lead Free

MARKING

SOT-23	TO-92		
☐ D9_D□ ☐ ☐ ☐ C: Lead Free G: Halogen Free	UTC 8050S□ G: Halogen Free Rank ← □ □□□ 1 Date Code		



■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	30	V
Collector-Emitter Voltage		V _{CEO}	20	V
Emitter-Base Voltage		V _{EBO}	5	V
Collector Current		Ι _C	700	mA
Collector Dissipation (T _A =25°C)	SOT-23	D	350	mW
	TO-92	P _C	1	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I _C = 1mA, I _B = 0	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E = 100μΑ, I _C =0	5			V
Collector Cut-Off Current	I _{CBO}	$V_{CB} = 30V, I_{E} = 0$			1	uA
Emitter Cut-Off Current	I _{EBO}	$V_{EB} = 5V, I_{C} = 0$			100	nA
	h _{FE1}	V _{CE} = 1V, I _C = 1mA	100			
DC Current Gain (note)	h _{FE2}	V _{CE} = 1V, I _C = 150 mA	120		400	
	h _{FE3}	V _{CE} = 1V, I _C = 500mA	40			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C = 500mA, I _B = 50mA			0.5	V
Base-Emitter Saturation Voltage		I _C = 500mA, I _B = 50mA			1.2	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	V _{CE} = 1V, I _C = 10mA			1.0	V
Current Gain Bandwidth Product	f⊤	V _{CE} = 10V, I _C = 50mA	100			MHz
Output Capacitance	Cob	V _{CB} = 10V, I _E = 0, f = 1MHz		9.0		pF

CLASSIFICATION OF h_{FE2}

RANK	С	D	E
RANGE	120-200	160-300	280-400



8050S

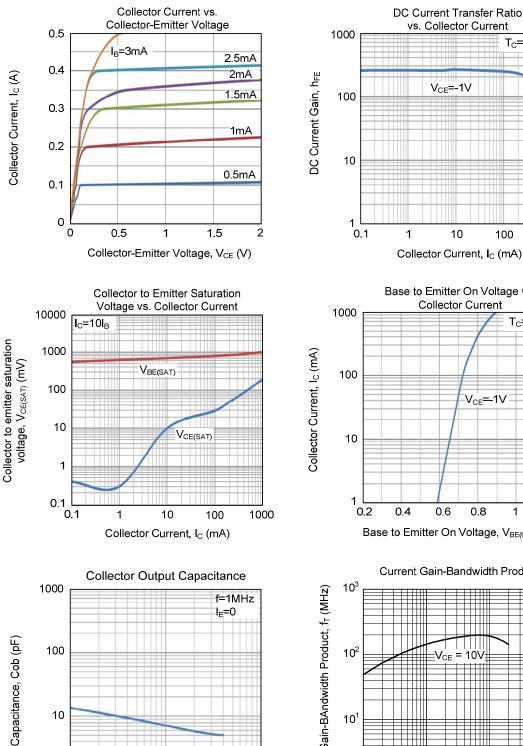
NPN SILICON TRANSISTOR

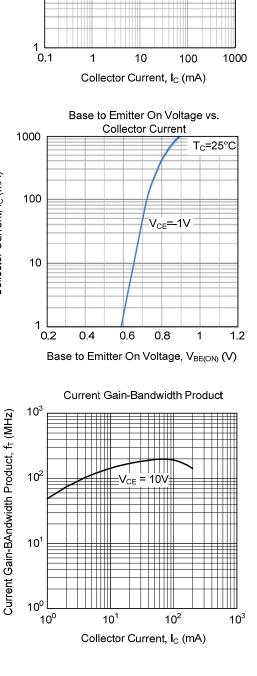
T_C=25°C

vs. Collector Current

V_{CE}=-1V

TYPICAL CHARACTERISTICS







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Collector-Base Voltage (V)

100

10

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UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

